



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DMBT4401

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

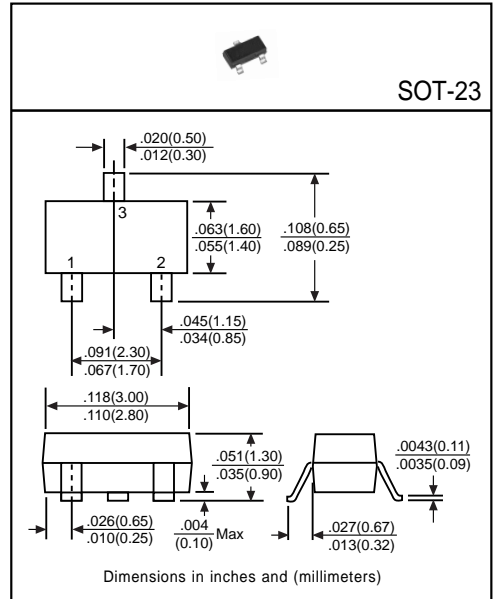
Designed for general purpose switching and amplifier applications.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	I _C	600	mA
Total Power Dissipation	P _D	225	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	60	-	-	V	I _C =100μA
Collector-Emitter Breakdown Voltage	BV _{CE0}	40	-	-	V	I _C =1mA
Emitter-Base Breakdown Voltage	BV _{EB0}	6	-	-	V	I _E =10μA
Collector Cutoff Current	I _{CEX}	-	-	100	nA	V _{CE} =35V, V _{EB} =0.4V
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)1}	-	-	0.4	V	I _C =150mA, I _B =15mA
	V _{CE(sat)2}	-	-	0.75	V	I _C =500mA, I _B =50mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)1}	-	-	0.95	V	I _C =150mA, I _B =15mA
	V _{BE(sat)2}	-	-	1.2	V	I _C =500mA, I _B =50mA
DC Current Gain ⁽¹⁾	h _{FE1}	20	-	-	-	I _C =0.1mA, V _{CE} =1V
	h _{FE2}	40	-	-	-	I _C =1mA, V _{CE} =1V
	h _{FE3}	80	-	-	-	I _C =10mA, V _{CE} =1V
	h _{FE4}	100	-	300	-	I _C =150mA, V _{CE} =1V
	h _{FE5}	40	-	-	-	I _C =500mA, V _{CE} =2V
Transition Frequency	f _T	250	-	-	MHz	I _C =20mA, V _{CE} =10V, f=100MHz
Output Capacitance	C _{ob}	-	-	6.5	pF	V _{CB} =5V, f=1MHz

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%